

Atomic-Scale Insights into Electronic, Structural, Dielectric, and Ferroelectric Properties of Ba(Zr, Ti)O₃ Perovskites

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Abstract: Ba(Zr, Ti)O₃ perovskites are promising lead-free piezoelectric and relaxor ferroelectric materials for energy storage and harvest devices, of which the ferroelectric mechanism has long been ambiguous. We theoretically investigated the ferroelectric mechanism from the electronic and atomic scale using first-principles calculation based on density functional theory and density functional perturbation theory. With increasing zirconium content, it is obtained a lattice expansion and a decrease in the ferroelectric polarization in agreement with experiment. An unstable zone-center phonon mode is observed in the polar ferroelectric phase, which tends to stabilize in the nonpolar paraelectric phase, which is associated with the engineering of the relative displacement of the B-site ions that alters the short-range force. The newly formed Ti/Zr (d_{zx}, d_{yz})-O ($2p_x, 2p_y$) π -type bonds are discovered to be the origin of the Ba(Zr, Ti)O₃ ferroelectric instability and polarization. Local relaxation strains caused by lattice misalignment of the ionic displacements of Ti ions and Zr ions suppress the polarization of Ba(Zr, Ti)O₃ by counteracting the off-centering of Ti ions and adjacent Zr ions in certain directions.

Keywords: ferroelectric polarization; ferroelectric instability; lattice dynamics; phonon dispersion; barium zirconate titanate

1 **1. Introduction**

2 Ferroelectric perovskite materials have been playing important roles in various
3 technological fields, such as capacitors, memories, sensors, actuators, and energy storage
4 and harvesting devices[1-5]. Among these, barium titanate (BaTiO_3) has attracted
5 extensive experimental and theoretical study since its discovery of ferroelectric behavior
6 in 1945 and 1946[6]. It undergoes a series of phase transitions from orthorhombic and
7 rhombohedral ferroelectric phases at low temperature into a tetragonal ferroelectric phase
8 with polarization along the [001] and then transforms to a cubic paraelectric phase with no
9 net polarization direction above 120 °C.

10 Understanding the origin of these phase transition of BaTiO_3 mainly focuses on the *soft-*
11 *phonon* models, which considers the transition as displacive and induced by the softening
12 of a zone-center TO mode as the transition temperature is approached[7]. Atomistic
13 displacement of Ti^{4+} cations from the $[\text{TiO}_6]$ octahedral center to an off-center position
14 causes the ferroelectric polarization[3]. It was understood that the balance of long-range
15 Coulomb interactions *versus* closed-shell ionic interactions, with the balance tipped by
16 smaller effects related to covalency between d-orbital of metallic ions and O 2p-orbital,
17 contributes to the ferroelectricity in perovskites[8]. First-principles calculations provide
18 support for this hybridization between O 2p states and B-site metallic ions d states, and the
19 giant anomalous Born effective charges reveal evidence for the ferroelectric instability
20 yielded by the large destabilizing Coulomb interaction[9, 10].

21 Dielectric and ferroelectric properties of BaTiO_3 can be tuned by introducing doping
22 elements into the cationic sub-lattice, which also broadens their application. For instance,
23 both permittivity and Curie temperature can be tunable in a large range in the BaTiO_3 –

1 SrTiO₃ solid solution [11]. Oxygen vacancies in BaTiO_{3-δ} produced itinerant electrons,
2 partially stabilizing the ferroelectric phases in metallic BaTiO_{3-δ} by screening strong
3 crystal field perturbations[12]. Temperature stability was broadened from -55 °C to 300 °C
4 for Ce-doped BaTiO₃[13], while the stable unipolar resistive switching characteristics was
5 demonstrated in Co-doped BaTiO₃[14]. Oxyhydride of BaTiO₃ was found to exhibit
6 hydride exchange and electronic conductivity[15]. With isovalent zirconium substituting
7 titanium, Ba(Zr_xTi_{1-x})O₃ (BZT) solid solutions exhibit decreasing ferroelectric transition
8 temperature from 405 K to ~350 K for $x = 0.15$ [16]. Considered as the promising lead-free
9 piezoelectric and relaxor ferroelectric systems, BZT solid solution have been receiving
10 continuous attention both experimentally[17-21] and theoretically[22, 23]. First-principles
11 supercell calculations on BaTi_{0.74}Zr_{0.26}O₃ showed Ti/Zr distribution determined the Ti
12 displacement and underlined the structural mechanisms involved random local strain
13 effects that lead to disordered Ti displacements[24]. The nonlinear permittivity of BZT for
14 $0.25 \leq x \leq 0.35$ was measured and the Zr⁴⁺ concentration was evidenced to control the
15 crossover from ferroelectric to relaxor behavior in isovalent BZT ceramics[25]. The
16 dynamic behavior of BZT ceramics with Zr concentration ($0.3 \leq x \leq 0.6$) was described by
17 the development of an order parameter via mean field theory[26]. For the case of BZT with
18 $x = 0.5$, the direct and the field-cooled susceptibility and the Edwards-Anderson order
19 parameter were calculated using first-principles based effective Hamiltonian approach[27].
20 Despite that large progress has been made in the past few years, there is still a lack of deep
21 understanding of the ferroelectric mechanism, which hinders the fine tuning and
22 meticulous engineering of the BZT ceramics. In this work, we report a detailed theoretical

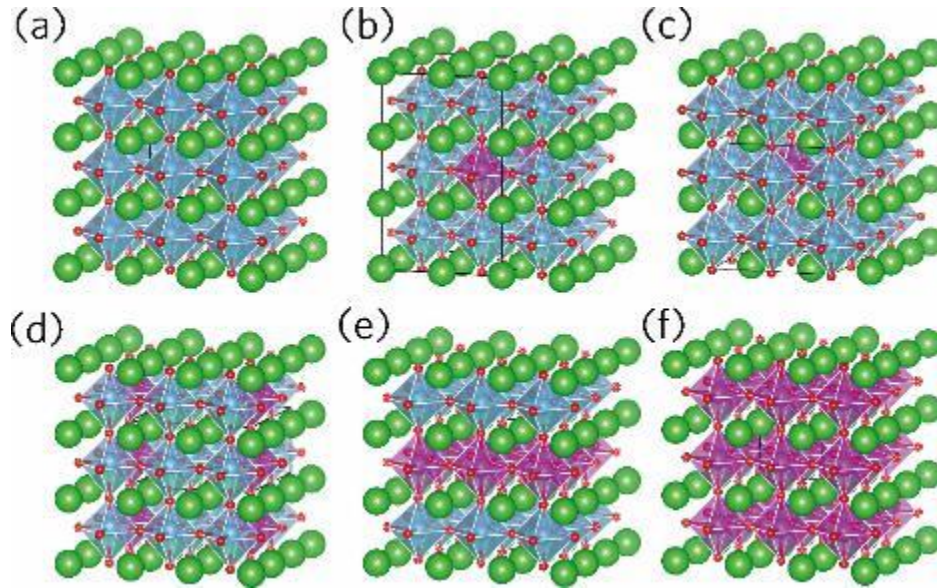
1 study aimed at revealing the intrinsic mechanisms of the ferroelectric properties of
2 $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ with $0 \leq x \leq 0.5$.

3 **2. Computational methods**

4 The polarization behaviors, lattice dynamics, electronic structure, band structure, and
5 orbital hybridization of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ with $0 \leq x \leq 0.5$ (Fig. 1) were computed from first-
6 principles calculations, which are based on density functional theory (DFT) as
7 implemented in Vienna ab initio simulation package (VASP) [28, 29]. Kohn-Sham energy
8 with respect to the basis set and the sampling of reciprocal space were employed to
9 minimize the variation in the lattice vibrations. The exchange and correlation effects are
10 treated within the generalized gradient approximation (GGA) with a Perdew–Burke–
11 Ernzerhof revised for solids (PBEsol) exchange-correlation functional[30]. The scalar-
12 relativistic projector augmented wave method (PAW) pseudopotentials used for BZT
13 models were constructed by the electron configurations as Ba $5s^25p^66s^2$ states, Ti
14 $3s^23p^63d^24s^2$ states, Zr $4s^24p^65s^24d^2$ and O $2s^22p^4$ states[31]. An energy cut-off of 600 eV
15 was chosen for the number of plane wave bases. Monkhorst-Pack mesh grid with $8 \times 8 \times 8$,
16 $8 \times 8 \times 2$, $8 \times 8 \times 8$, $8 \times 4 \times 2$, and $8 \times 8 \times 2$ special k-point mesh for BZT models with $x = 0, 0.083$,
17 $0.125, 0.167, 0.25$, and 0.5 , respectively, were carried out for the special points sampling
18 integration over the Brillouin zone. [32] The energy tolerance was 1×10^{-8} eV/atom, while
19 the force tolerance was set to 0.001 eV/Å.

20 Hybrid functional HSE06 is employed to obtain accurate band structures. Born effective
21 charges, phonon frequencies and dielectric properties are calculated using density
22 functional perturbation theory (DFPT) [33, 34] implanted in VASP code and post-
23 processed with the PHONOPY code[35]. The force constants and the dynamical matrix

1 were obtained from the Hellmann–Feynman forces calculated with small individual
2 displacements of non-equivalent atoms. Both density functional perturbation theory (DFPT)
3 approaches [36] and the finite displacement supercell approaches[37] were tested to
4 construct and evaluate force constants, which produced similar results within the variance
5 in the mode energies of 5 cm^{-1} . The macroscopic electronic polarization is calculated by
6 using the Berry phase method[38]. The fitted energy-polarization curve and temperature-
7 dependence relationship were performed using a homemade program, which is developed
8 based on electrostatics displacement field and Landau-Ginsburg-Devonshire (LGD) theory.



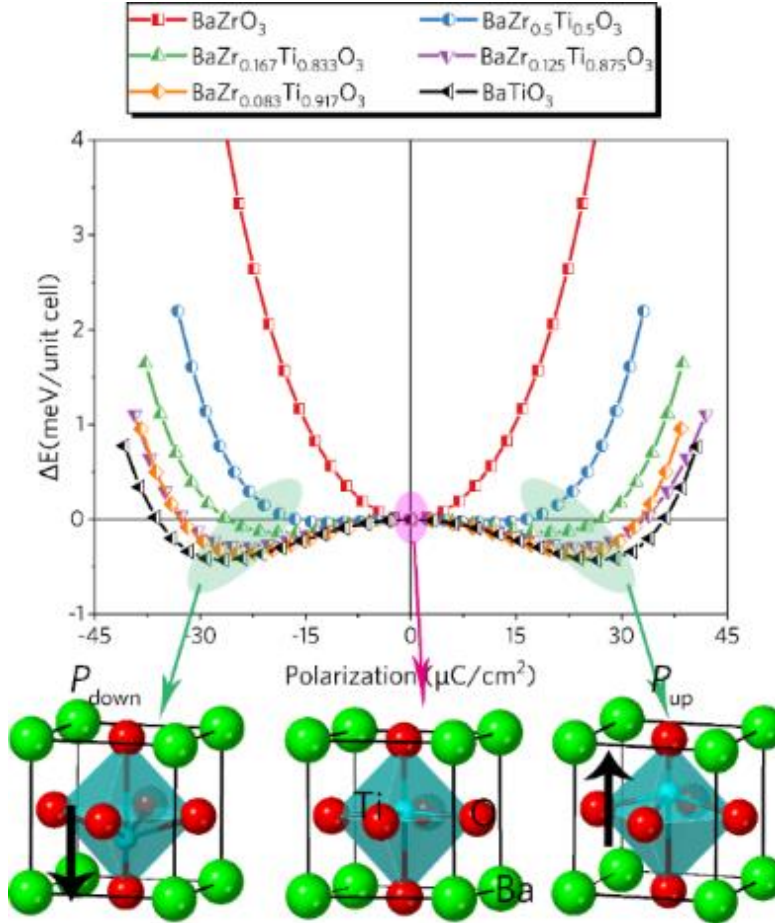
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10 Fig. 1. Lattice models of Ba(Zr, Ti)O₃. (a) $x = 0$, (b) $x = 0.083$, (c) $x = 0.125$, (d) $x = 0.25$, (e) $x = 0.5$.
11 (f) $x = 1.0$. The Ti cation represented by a cyan sphere is at the center of the unit cell and is six-fold
12 coordinated to oxygen represented by a red sphere. Ba cation is represented by a green sphere. Zr cation
13 is represented by a blue sphere.

14

15 3. Results and discussion

1 BZT superlattices were constructed based on tetragonal BaTiO₃ lattice with Zr-substitution
2 of Ti. Fig. 1 shows the Ba(Zr, Ti)O₃ structure with various contents of Zr. For the pure
3 tetragonal BaTiO₃, the calculated lattice constant $a = b = 3.98 \text{ \AA}$, and $c = 4.03 \text{ \AA}$, which is
4 in great consistence with experimental results[39]. The calculated equilibrium lattice
5 constants of Ba(Zr_xTi_{1-x})O₃ with $0 \leq x \leq 0.5$ are listed in Table 1. The lattice parameters of
6 Ba(Zr_xTi_{1-x})O₃ were found to increase with substitution content, which is also
7 experimentally observed in the polycrystalline samples of Zr-doped BaTiO₃ prepared by
8 conventional solid state reaction method [40].

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2 Fig. 2. Total energy change due to bulk ferroelectric soft-mode distortion is calculated as a function of
 3 ferroelectric polarization for different chemical composition of $\text{Ba}(\text{Zr}, \text{Ti})\text{O}_3$. Bottom panels show the
 4 atomic configuration of BaTiO_3 with the polarization switching.

5 Table 1 Computational parameters of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ with $0 \leq x \leq 0.5$ after geometry relaxation, including
 6 the converged energy and force threshold, the plane-wave cutoff and k-point mesh.

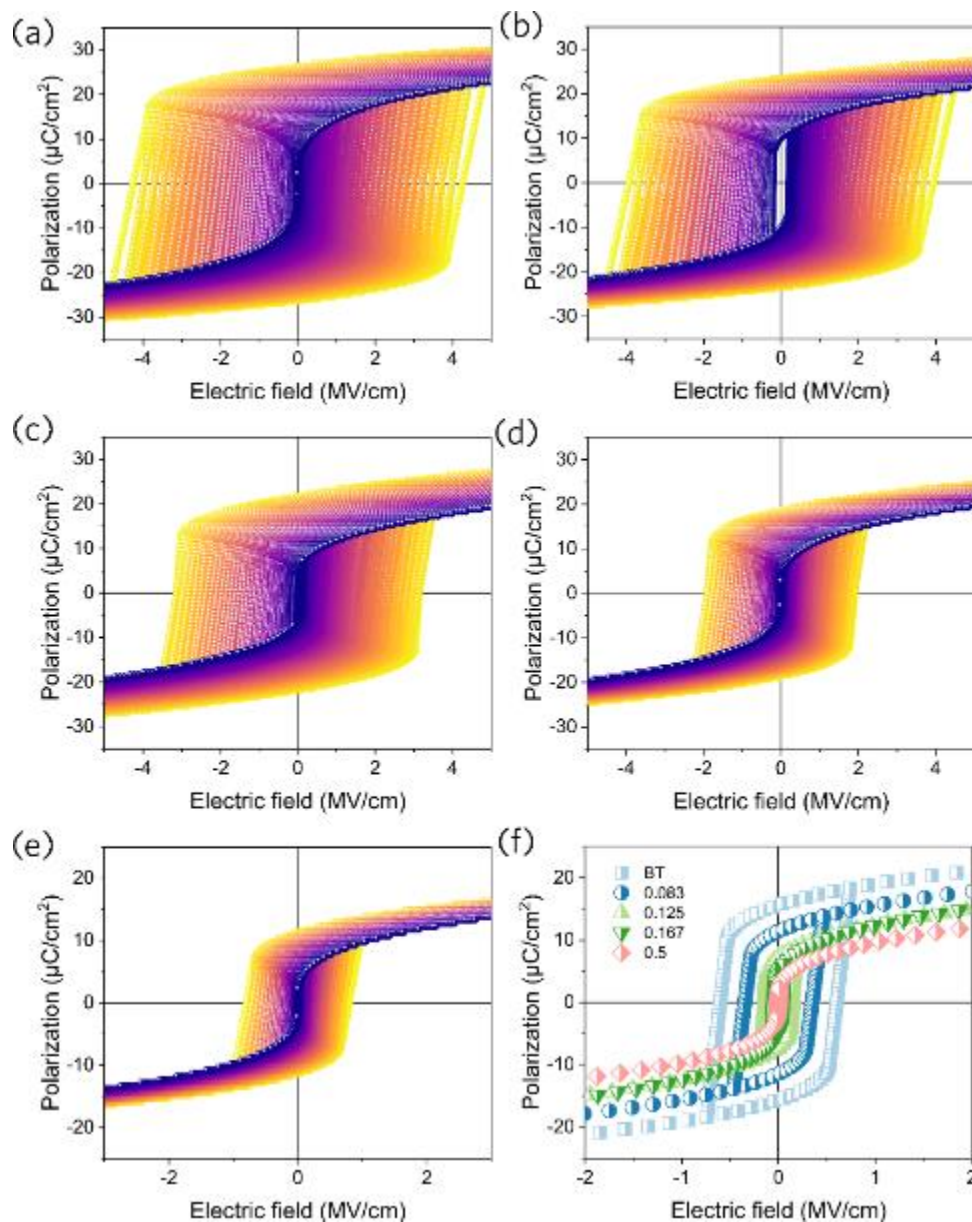
x	a (\AA)	b (\AA)	c (\AA)	V (\AA^3)	Cutoff (eV)	k points	Energy (eV/atom)	Forces (eV/ \AA)
0.0	3.98	3.98	4.03	64.13	600	$8 \times 8 \times 8$	10^{-8}	10^{-3}
0.083	8.03	8.03	12.6 9	818.97	600	$8 \times 8 \times 2$	10^{-8}	10^{-3}
0.125	8.01	8.01	8.15	522.52	600	$8 \times 8 \times 8$	10^{-8}	10^{-3}
0.167	4.11	8.19	12.2 8	413.25	600	$8 \times 4 \times 2$	10^{-8}	10^{-3}
0.25	8.04	8.04	4.15	268.03	600	$8 \times 8 \times 2$	10^{-8}	10^{-3}
0.5	4.19	4.19	8.33	146.07	600	$8 \times 8 \times 2$	10^{-8}	10^{-3}

1.0	4.19	4.19	4.19	73.77	600	8×8×8	10 ⁻⁸	10 ⁻³
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1 Variation of total energy affected by the bulk ferroelectric soft-mode distortion as a
 2 function of ferroelectric polarization for different chemical composition of Ba(Zr, Ti)O₃.
 3 is obtained, as shown in Fig. 2. Bottom panels show the atomic configuration of BaTiO₃
 4 with the polarization switching. The Ti cation represented by a cyan sphere is at the center
 5 of the unit cell and is six-fold coordinated to oxygen represented by a red sphere. Ba cation
 6 is represented by a green sphere. The total energy of paraelectric phase is taken as a
 7 reference. The double minima show the down and up polarization variations. For the
 8 paraelectric phase of BaTiO₃ with cubic structure, B-site cations are in the center of crystal
 9 lattice and symmetric to the neighboring ions. The ferroelectric soft-mode distortion is
 10 characterized by the shift of the B-site cation such as Zr and Ti cations with respect to the
 11 surrounding O-ion octahedron. A net macroscopic electrical polarization is produced
 12 through breaking inversion symmetry by the internal distortion. The total energy of
 13 paraelectric phase is taken as a reference, while the minima of double-curve represents the
 14 ferroelectric phase. As seen from Fig. 2, ferroelectric BaTiO₃ and Ba(Zr, Ti)O₃ exhibit a
 15 deep double-well profile with two global energy minimum as the off-center position,
 16 similar to what is shown by other reports about ferroelectric materials such as LaFeO₃[41],
 17 thin layer of ferroelectric Hf_{0.5}Zr_{0.5}O₂ [42], multiferroic BiFeO₃ [43] and others. On the
 18 other hand, BaZrO₃ exhibits a single well profile with only one energy minimum at the
 19 central position. The calculated polarization for the ferroelectric tetragonal BaTiO₃ is 29.1
 20 μC/cm² which is in good agreement with other results[9, 44]. With the increase of Zr cation
 21 amount, the spontaneous polarization of Ba(Zr, Ti)O₃ displays a decreasing trend, which is
 22 observed in the experimental ceramics[17, 45]. For the case of $x = 0.083$, the ferroelectric
 23 polarization of Ba(Zr, Ti)O₃ is 27.2 μC/cm². The ferroelectric polarization of Ba(Zr, Ti)O₃

1 is $26.5 \mu\text{C}/\text{cm}^2$ for $x = 0.167$, $21.1 \mu\text{C}/\text{cm}^2$ for $x = 0.25$, and $23.0 \mu\text{C}/\text{cm}^2$ for $x = 0.5$,
2 respectively. At the same time, the well-depth of energy-polarization profile exhibits
3 reduction as the increase of Zr amount. The reduction in well-depth and spontaneous
4 polarization is attributed to the larger ionic offset and stronger hybridization of Zr 4d to O
5 2p and Ba 3d to O 2p states.

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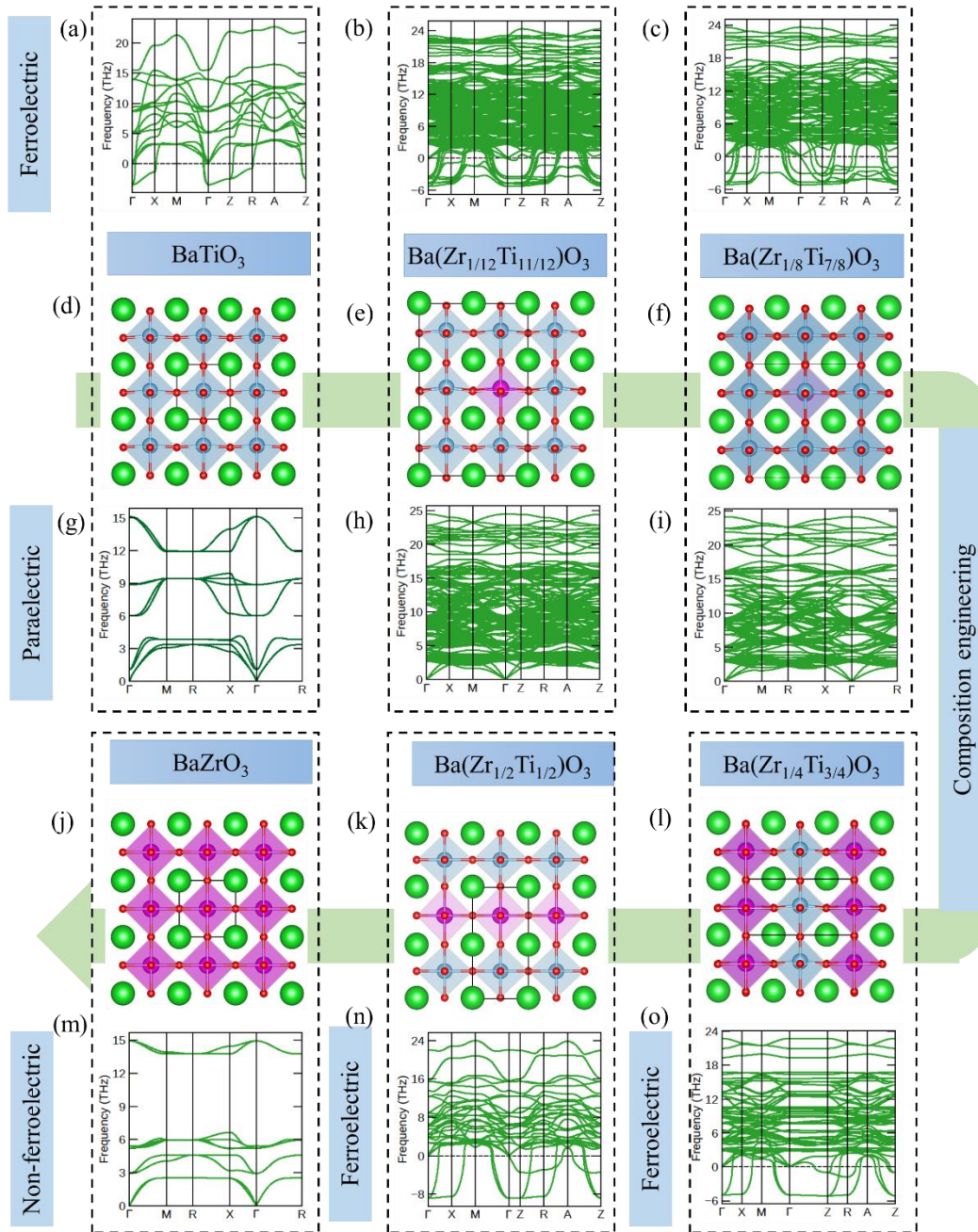
1 Fig. 3. Temperature dependence of the ferroelectric hysteresis of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ with various
2 composition. (a) $x = 0$, (b) $x = 0.083$, (c) $x = 0.125$, (d) $x = 0.167$, (e) $x = 0.5$. (f) Composition
3 dependence of the ferroelectric hysteresis of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ at 295 K.

4 The temperature dependence of ferroelectric hysteresis is calculated from
5 phenomenological Landau-Ginsburg-Devonshire (LGD) theory, as shown in Fig. 3.
6 Ferroelectric loops of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ are found to shrink with the increase of temperature,
7 which result from the phase transition of the ferroelectric tetragonal phase to the
8 paraelectric cubic phase. At temperatures far below phase transition temperature, near-
9 square ferroelectric P-E loops with high remnant polarization are observed. As the
10 temperature increases, remnant polarization decreases and the coercive field decreases
11 simultaneously, which is in good consistence with the experimental results of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})$ -
12 O_3 ceramics [46-48]. In Fig. 3(f), with the increased amount of zirconium ions, the
13 remnant polarization, maximum polarization and nonlinearity are reduced, which is
14 observed in the manganese-doped $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ ceramics [49].

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16 Phonon dispersion curves of various BZT models are achieved. Fig. 4(a) shows the phonon
17 dispersion for tetragonal BaTiO_3 with the structure at the minimum state of double well
18 landscape. The transverse optic modes are unstable at the Γ point and become stable along
19 Γ -M and Γ -R directions resulted from the volume elongation along [001] directions, which
20 is in good agreement with other computational and experimental results[50-52]. Analysis
21 of phonon dispersion for $\text{Ba}(\text{Zr}, \text{Ti})\text{O}_3$ with various composition shown in Fig. 4(b,c)
22 reveals the disappearance of imaginary frequencies at the Γ point, indicating that the
23 ground state of paraelectric $\text{Ba}(\text{Zr},\text{Ti})\text{O}_3$ is nonpolar tetragonal phase. In contrast, the
24 ferroelectric $\text{Ba}(\text{Zr},\text{Ti})\text{O}_3$ shows highly unstable phonon modes. The strongest instabilities
25 are observed at the Γ point with an irreducible representation Γ_{15} . For the case of

1 Ba(Zr_xTi_{1-x})O₃ with $x = 0.083$ and 0.125 , all phonon modes at the high K-point boundaries
2 are unstable with a maximum imaginary frequency of $5.59i$ THz, and $5.20i$ THz,
3 respectively. For the case of pure BaZrO₃ containing no Ti ions, all the transverse optic
4 modes are stable at the high symmetry point. For the case of Ba(Zr_xTi_{1-x})O₃ with $x = 0.25$
5 and 0.5 , phonon branches along G-X and G-Z-R are unstable while the phonon mode at
6 M point is stable. The maximum imaginary frequencies are $4.96i$ THz and $8.83i$ THz. The
7 imaginary modes are derived from the relative translation of B-site ions relative to O ions.
8 This suggests that the solidification of the Γ_{15} unstable mode in the tetragonal ferroelectric
9 phase would directly drive the system to the nonpolar state. We thus performed a full
10 relaxation of the cell. Indeed, we obtained the nonpolar state phase as shown in Fig. 4(g,h,i).
11 Experimentally, paraelectric phase of BaTiO₃ and Ba(Zr, Ti)O₃ are nonpolar state, while
12 the ferroelectric phases are polar states with the characteristic of ferroelectric hysteresis.
13 Herein the direct proof is provided for the transition between polar state to nonpolar states
14 as evidenced from the phonon dispersion curve, which contradicts previous reports that
15 state the existence of unstable phonon mode in nonpolar paraelectric phase.

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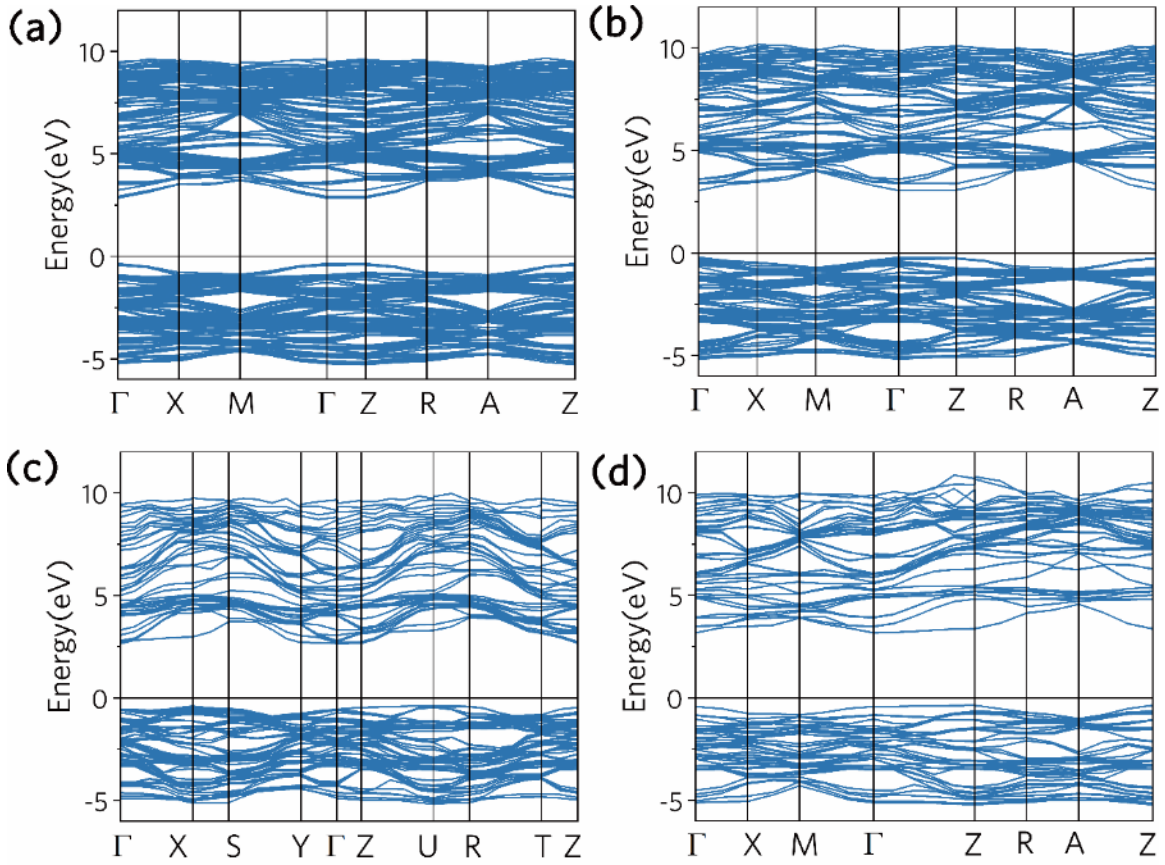
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Fig. 4. Phonon dispersion curves of paraelectric and ferroelectric phase of Ba(Zr, Ti)O₃ under different composition, together with the corresponding lattice structures. Imaginary frequencies are plotted as negative values. Paraelectric phase shows all stable phonon modes, while ferroelectric phase shows unstable imaginary phonon branches.

1 Electronic band structure along the high symmetry directions in the first Brillouin zone is
2 presented in Fig. 5. Hybrid exchange functional HSE06 is employed, which can give more
3 accurate band gaps than the conventional GGA or LDA functional. The band gap of
4 BaTiO₃ derived from the HSE06 calculations is 3.00 eV, which is in good agreement with
5 the experimental and other theoretical values [53, 54]. As the zirconium content increases,
6 the band structure become more complex with increased band levels. The valence band
7 near the Fermi surface of BZT are in energy from -5 to 0 eV and the conduction band is in
8 the energy from 2 to 10 eV, enabling the whole system to exhibit semiconductor properties.
9 HSE06 bandgaps for Ba(Zr_xTi_{1-x})O₃ where $x = 0.083, 0.125, 0.167, \text{ and } 0.25$ are 3.17 eV,
10 3.20 eV, 3.05 eV, 3.04 eV and 3.6 eV, respectively. The increased bandgap provides
11 support for the experimental improvement in insulation ability and decline in dielectric loss.

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Fig. 5. Band structure of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ from HSE06 calculations with various composition. (a) $x =$

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0.083, (b) $x = 0.125$, (c) $x = 0.167$, (d) $x = 0.25$.

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To further analyze the origin of ferroelectric properties, the total and partial density of

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states of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ are studied as shown in Fig. 6 and Fig. 8. The symmetric spin up

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and spin down states reveals no magnetism. From the energy band level in Fig. 6(b), the

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lower valence band located at -60eV, -50eV and -36eV is mainly occupied by the Ti 4s, Zr

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5s and Ti 3p orbitals. Zr 4p and Ba 6s orbitals contribute to the energy band at -27eV, O

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2s orbital contributes to the energy band at -18eV, and Ba 5p orbital contributes to the

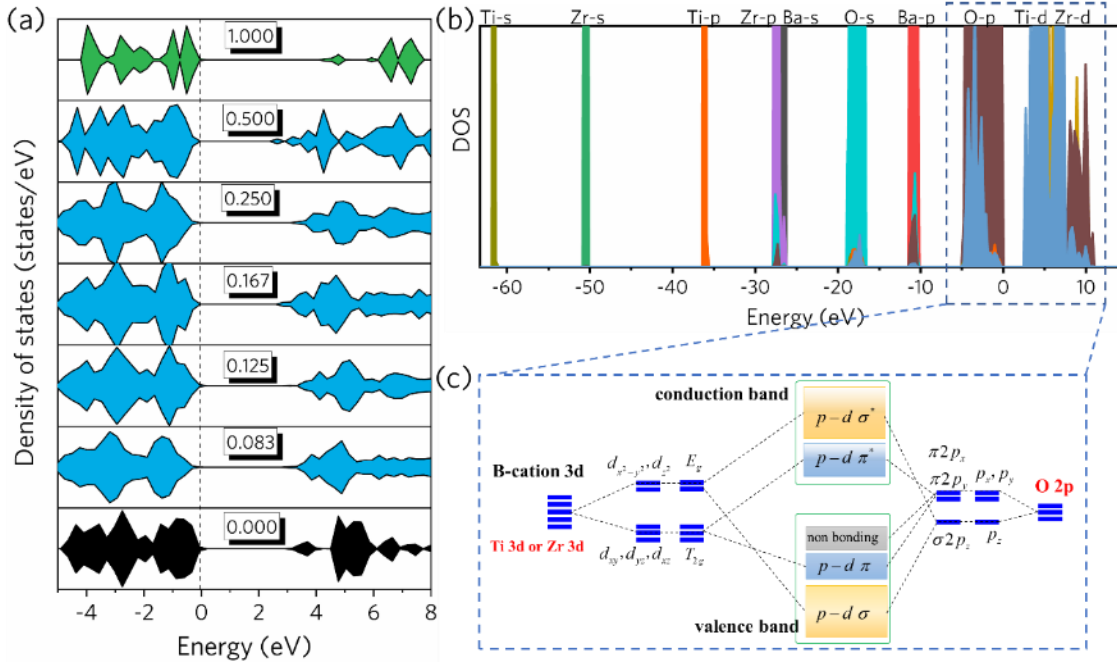
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energy band at -11eV. The valence band in the energy range of -5 eV to 0 eV is mainly

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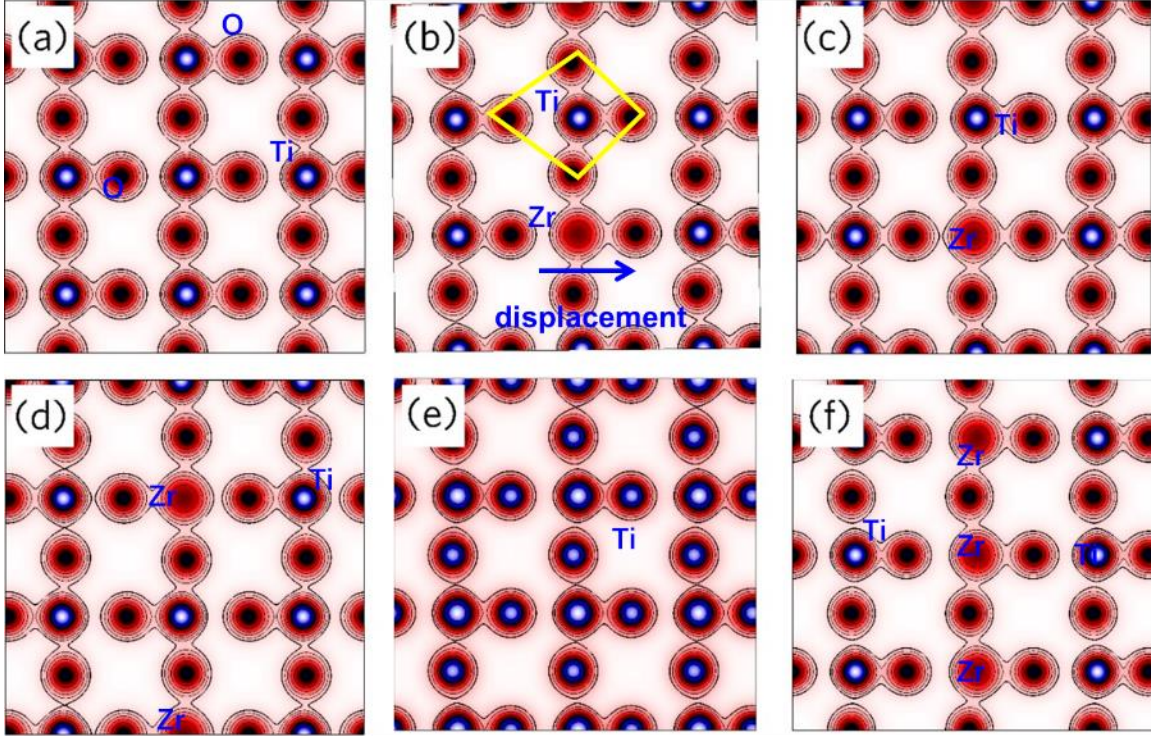
attributed by the O 2p states, with some mixing of Ti 3d and Zr 4d states shown in Fig.

1 8(a-b). The conduction band in the energy range of 2 eV to 10 eV is mainly attributed to
 2 the Ti 3d states, with some mixing of O 2p and Zr 4d states as shown in Fig. 8(a-b). This
 3 hybridization of Ti 3d, O 2p, and Zr 4d is a characteristic for ferroelectric Ba(Zr_xTi_{1-x})O₃.



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Fig. 6.(a) Compositional dependence of total density of states of Ba(Zr_xTi_{1-x})O₃, revealing no magnetism from the symmetric spin up and spin down states. (b) Energy band level and (c) molecular orbital diagram of Ba(Zr_xTi_{1-x})O₃.



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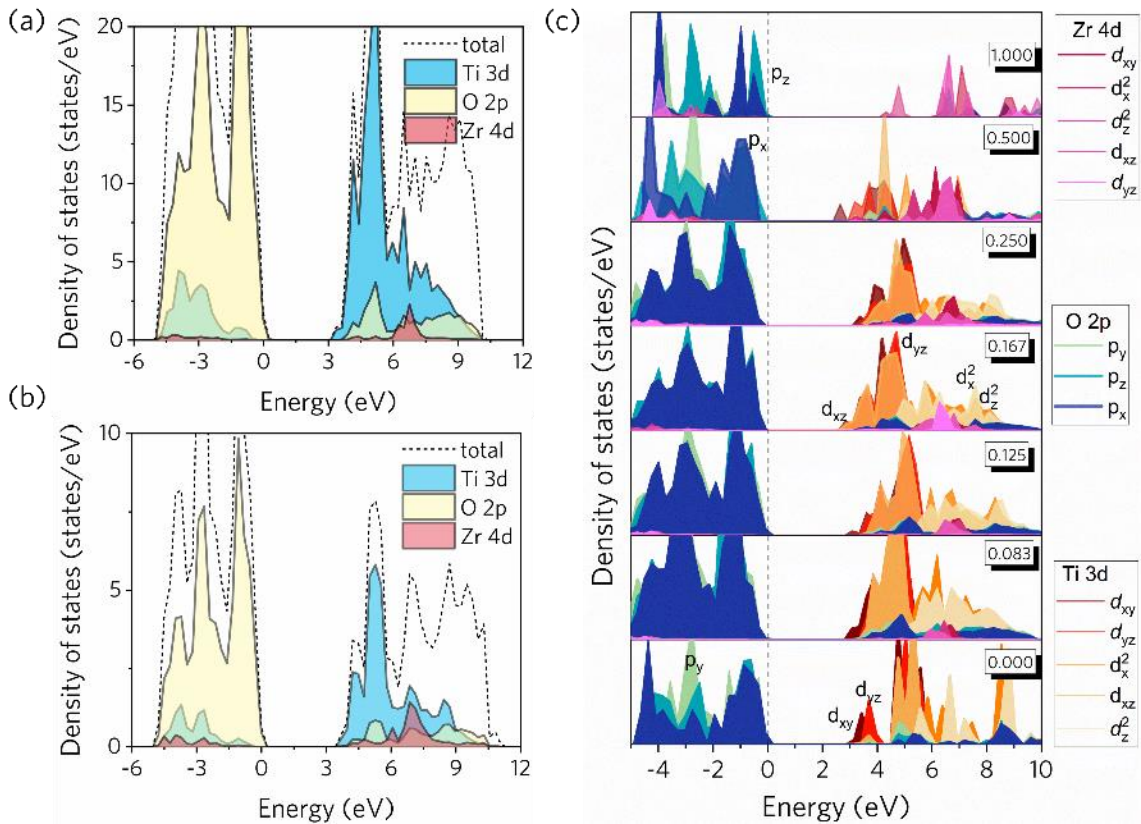
2 Fig. 7. Charge density mapping of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ with various composition. (a) $x = 0$, (b) $x = 0.083$,
 3 (c) $x = 0.125$, (d) $x = 0.167$, (e) $x = 0.25$, (f) $x = 1$.

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5 To obtain deeper analysis of the orbital hybridization, charge density mapping, molecular
 6 orbitals and Im-decomposed density of states of $\text{Ba}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ are investigated, as shown
 7 in Fig. 6(c), Fig. 7, and Fig. 8(c), respectively. Five d-orbitals of B-site Ti or Zr split into
 8 two types, namely, triply degenerated $T_{2g}(d_{xy}, d_{yz}, d_{zx})$ in the lower energy level and doubly
 9 degenerated $E_g(d_{x^2-y^2}, d_{z^2})$ in the higher energy level. The hybridization of $E_g(d_{x^2-y^2}, d_{z^2})$
 10 with O 2pz orbitals form the p-d σ -type bond at valence bond and p-d σ -type anti-bond at
 11 conduction bond, which further construct the three-dimensional framework of oxygen
 12 octahedron. The hybridization of $T_{2g}(d_{xy}, d_{yz}, d_{zx})$ with O 2p (p_x, p_y) form the p-d π -type
 13 bond at valence bond and p-d π -type anti-bond at conduction bond. The introduction of Zr
 14 ions induced the off-center B-site displacement (Fig. 7), which split T_{2g} orbitals into d_{xy}
 15 and (d_{yz}, d_{zx}) orbitals. Therefore, strong hybridization of Ti $3d_{zx}$ -O $2p_x$ π -type bond, Zr $4d_{zx}$ -

1 O2p_x π -type bond, Ti 3d_{yz}-O2p_y π -type bond, and Ti 3d_{yz}-O2p_y π -type bond is produced.
 2 This π -type bond is the origin of ferroelectric properties and the dynamic instability of
 3 Ba(Zr_xTi_{1-x})O₃. It was found that the substitution of Zr for Ti strongly favors short-range
 4 repulsive forces, while the larger size of Zr ions locally favors long-range interactions
 5 along the O-Ti-O-Ti-O chain[55]. Local relaxation strains caused by lattice misalignment
 6 of the ionic displacements of Ti and Zr ions therefore suppress the polarization of
 7 Ba(Zr_xTi_{1-x})O₃ compared with BaTiO₃ by cancelling out the off-centering of Ti ions and
 8 adjacent Zr ions in certain directions.

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12 Fig. 8. Density of states of Ba(Zr_xTi_{1-x})O₃ from HSE06 calculations with various composition. (a) x =
 13 0.083, (b) x = 0.25, (c) Compositional dependence *lm*-decomposed density of states of O2p, Ti 3d, and
 14 Zr 4d orbitals.

1 **4. Conclusions**

2 In this work, we investigated the polarization behaviors, lattice dynamics, electronic
3 structure, band structure, and orbital hybridization of Ba(Zr, Ti)O₃ and analyzed the origin
4 of the ferroelectric mechanism from the electronic and atomic point of view using first-
5 principles calculations. Substitution of Zr with Ti ions raises the lattice parameters and
6 reduces the ferroelectric polarization, which was also observed in the experimental
7 ceramics and confirmed high validity of the as-performed calculations. The increasing
8 bandgap with increasing zirconium content provides support for the experimental
9 improvement in insulation ability and reduction in dielectric loss. An unstable zone-center
10 phonon mode is observed for the polar ferroelectric phase, which becomes stabilized in the
11 nonpolar paraelectric phase associated with the modification of the short-range forces by
12 engineering the relative displacements of B-site ions. The newly formed Ti/Zr (d_{zx}, d_{yz})-O
13 ($2p_x, 2p_y$) π -type bond is discovered to be the origin of the ferroelectric instability and the
14 ferroelectric polarization of Ba(Zr, Ti)O₃. Local relaxation strains caused by lattice
15 misalignment of the ionic displacements of Ti and Zr ions suppress the polarization of
16 Ba(Zr, Ti)O₃ compared with BaTiO₃ by cancelling out the off-centering of Ti ions and
17 adjacent Zr ions in certain directions.

18

19 **Declaration of competing interest**

20 The authors declare that they have no known competing financial interests or personal
21 relationships that could have appeared to influence the work reported in this paper.

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3 Agricultural University and the National Natural Science Foundation of China (Grant No.
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5 the calculations were performed on Tianhe new generation supercomputer.

6 **Data Availability Statement:**

7 The data that support the findings of this study are available from the corresponding author
8 upon reasonable request.

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